FAIRCHILD
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FQP12P20

P-Channel QFET® MOSFET

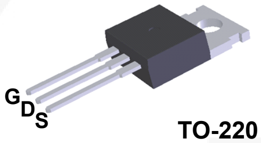
-200 V, -11.5 A, 470 mΩ

Description

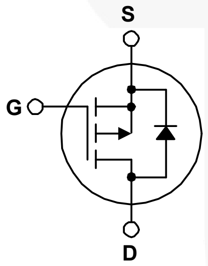
This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- -11.5 A, -200 V, $R_{DS(on)}$ = 470 mΩ (Max.) @ V_{GS} = -10 V, I_D = -5.75 A
- Low Gate Charge (Typ. 31 nC)
- Low Crss (Typ. 30 pF)
- 100% Avalanche Tested
- RoHS Compliant



TO-220



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted.

Symbol	Parameter	FQP12P20	Unit
V_{DSS}	Drain-Source Voltage	-200	V
I_D	Drain Current - Continuous (T_C = 25°C)	-11.5	A
	- Continuous (T_C = 100°C)	-7.27	A
I_{DM}	Drain Current - Pulsed (Note 1)	-46	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	810	mJ
I_{AR}	Avalanche Current (Note 1)	-11.5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-5.5	V/ns
P_D	Power Dissipation (T_C = 25°C)	120	W
	- Derate above 25°C	0.96	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.	300	°C

Thermal Characteristics

Symbol	Parameter	FQP12P20	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.04	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

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Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP12P20	FQP12P20	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics

T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = -250 µA	-200	--	--	V
ΔBV_{DSS} / ΔT	Breakdown Voltage Temperature Coefficient	I_D = -250 µA, Referenced to 25°C	--	-	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -200 V, V_{GS} = 0 V	--	--	-1	µA
		V_{DS} = -160 V, T_C = 125°C	--	--	-10	µA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250 µA	-3.0	--	-5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = -10 V, I_D = -5.75 A	--	0.36	0.47	Ω
g_{FS}	Forward Transconductance	V_{DS} = -40 V, I_D = -5.75 A	--	6.4	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -25 V, V_{GS} = 0 V, f = 1.0 MHz	--	920	1200	pF
C_{oss}	Output Capacitance		--	190	250	pF
C_{rss}	Reverse Transfer Capacitance		--	30	40	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = -100 V, I_D = -11.5 A, R_G = 25 Ω (Note 4)	--	20	50	ns
t_r	Turn-On Rise Time		--	195	400	ns
$t_{d(off)}$	Turn-Off Delay Time		--	40	90	ns
t_f	Turn-Off Fall Time		--	60	130	ns
Q_g	Total Gate Charge	V_{DS} = -160 V, I_D = -11C5 A, V_{GS} = -10 V (Note 4)	--	31	40	nC
Q_{gs}	Gate-Source Charge		--	8.1	--	nC
Q_{gd}	Gate-Drain Charge		--	16	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	-11.5	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	-46	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = -11.5 A	--	--	-5.0	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = -11.5 A, dI_F / dt = 100 A/µs	--	180	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.44	--	µC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. L = 9.2 mH, I_{AS} = -11.5 A, V_{DD} = -50 V, R_G = 25 Ω, starting T_J = 25°C.
3. $I_{SD} \leq$ -11.5 A, di/dt $\leq$ 300 A/µs , $V_{DD} \leq BV_{DSS,}$ starting T_J = 25°C.
4. Essentially independent of operating temperature.

Typical Characteristics

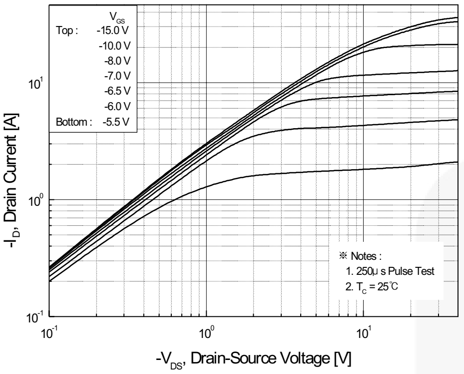


Figure 1. On-Region Characteristics

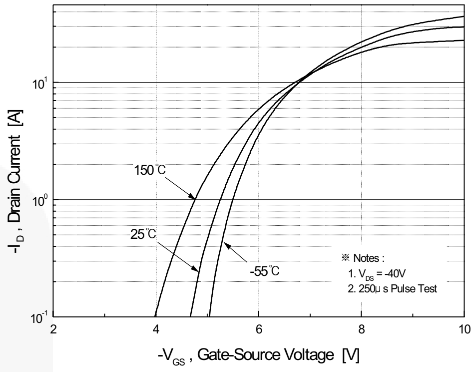


Figure 2. Transfer Characteristics

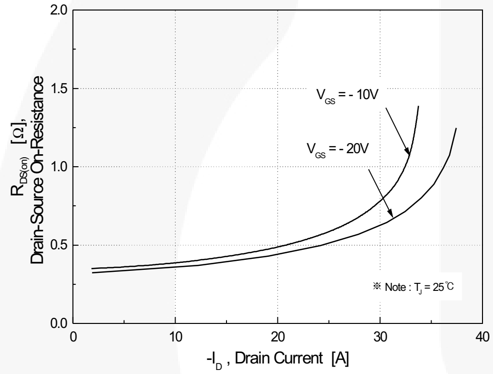


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

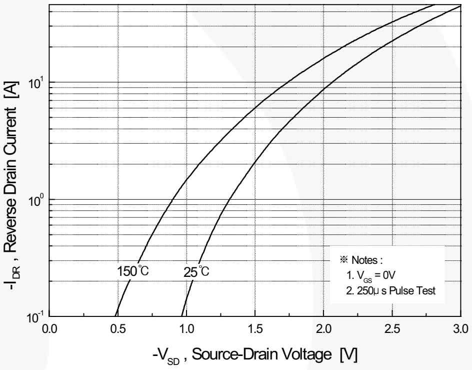


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

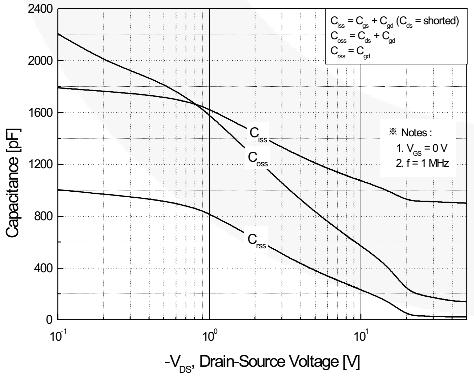


Figure 5. Capacitance Characteristics

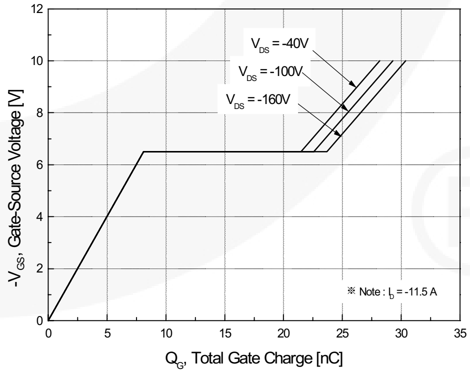


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

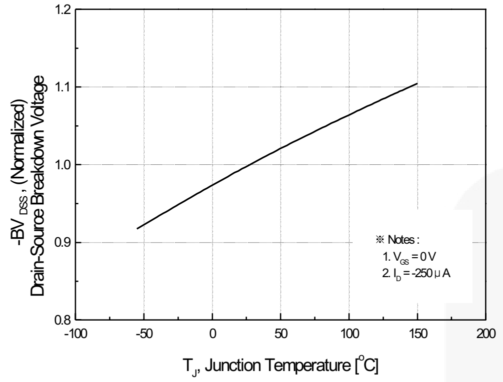


Figure 7. Breakdown Voltage Variation vs. Temperature

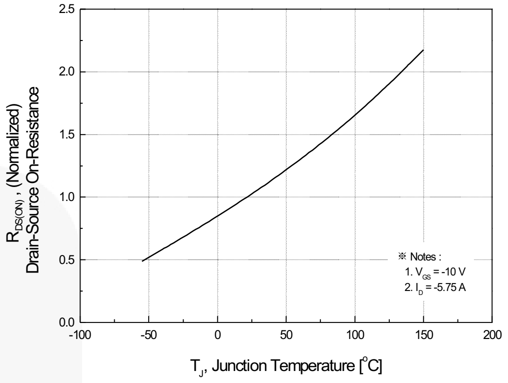


Figure 8. On-Resistance Variation vs. Temperature

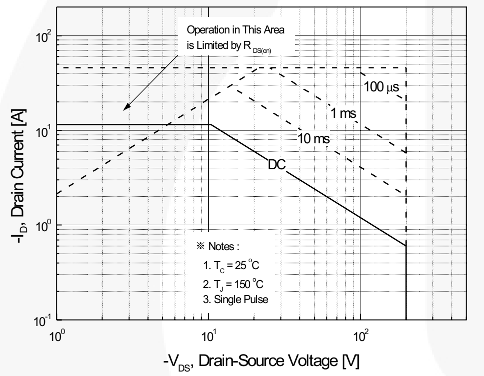


Figure 9. Maximum Safe Operating Area

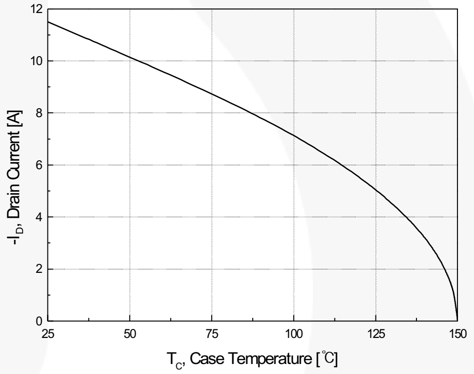


Figure 10. Maximum Drain Current vs. Case Temperature

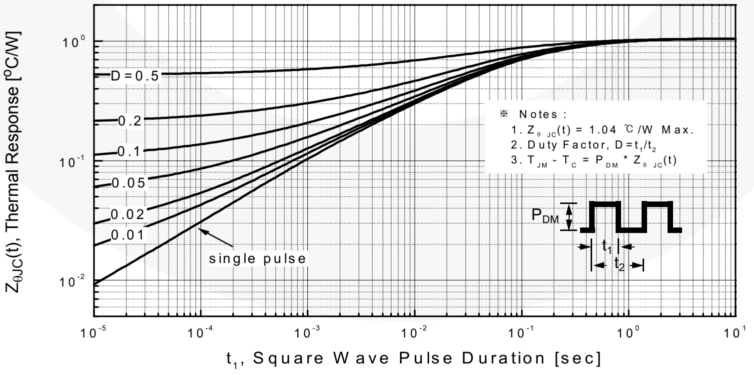


Figure 11. Transient Thermal Response Curve

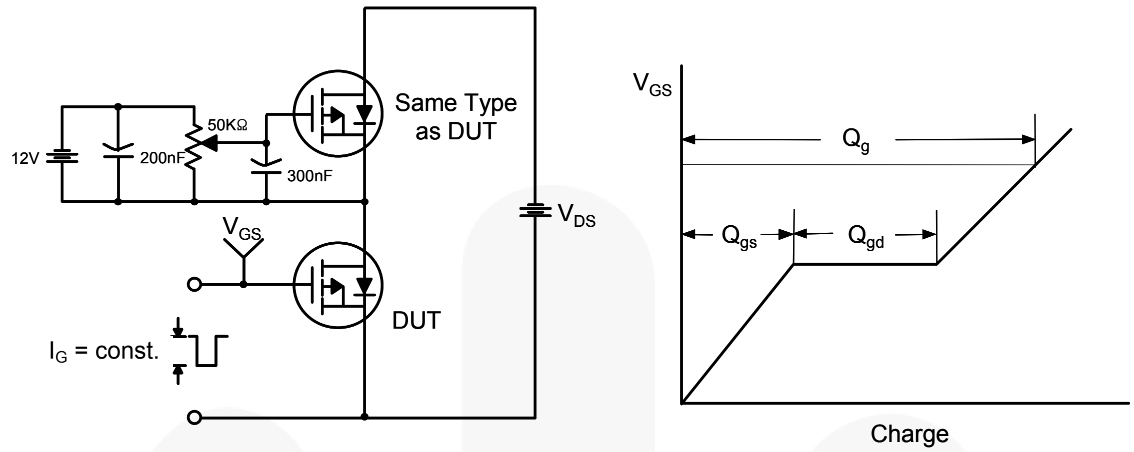


Figure 12. Gate Charge Test Circuit & Waveform

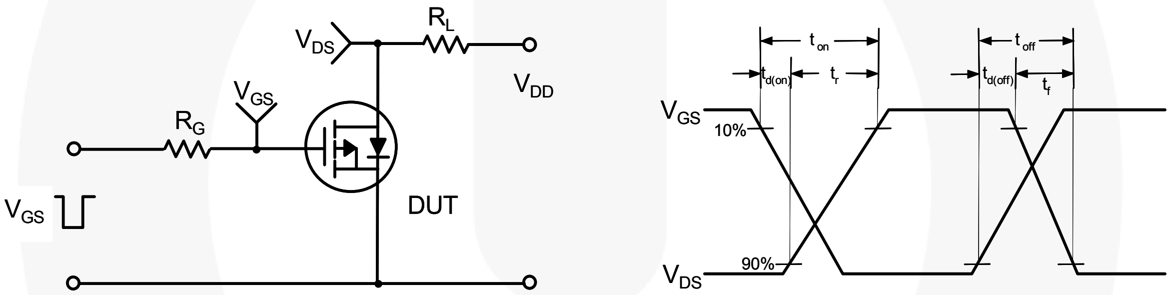


Figure 13. Resistive Switching Test Circuit & Waveforms

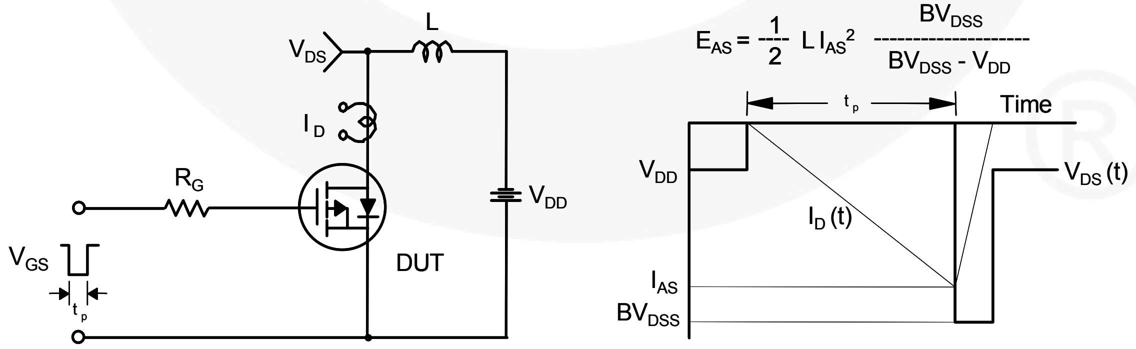


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

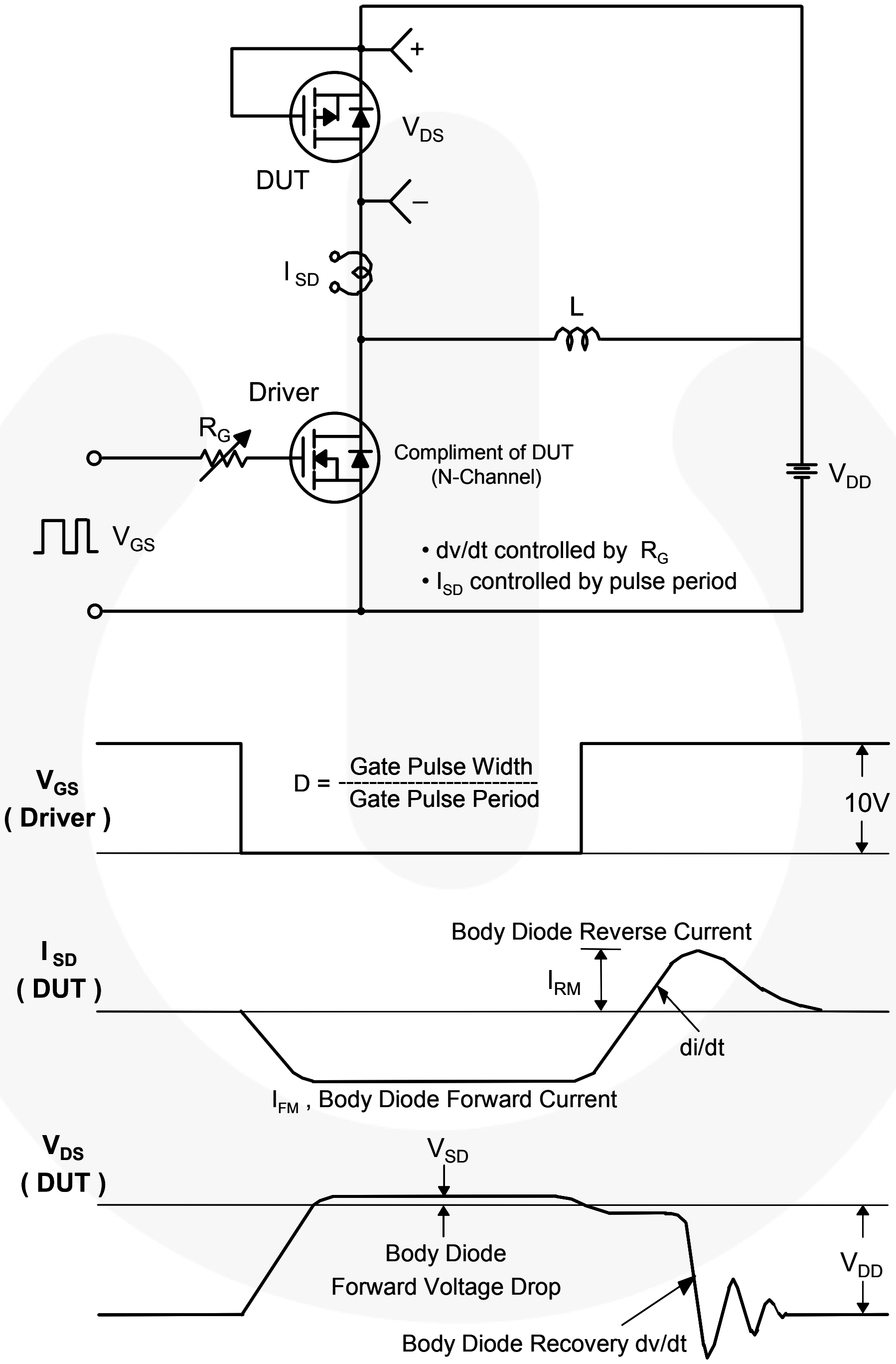
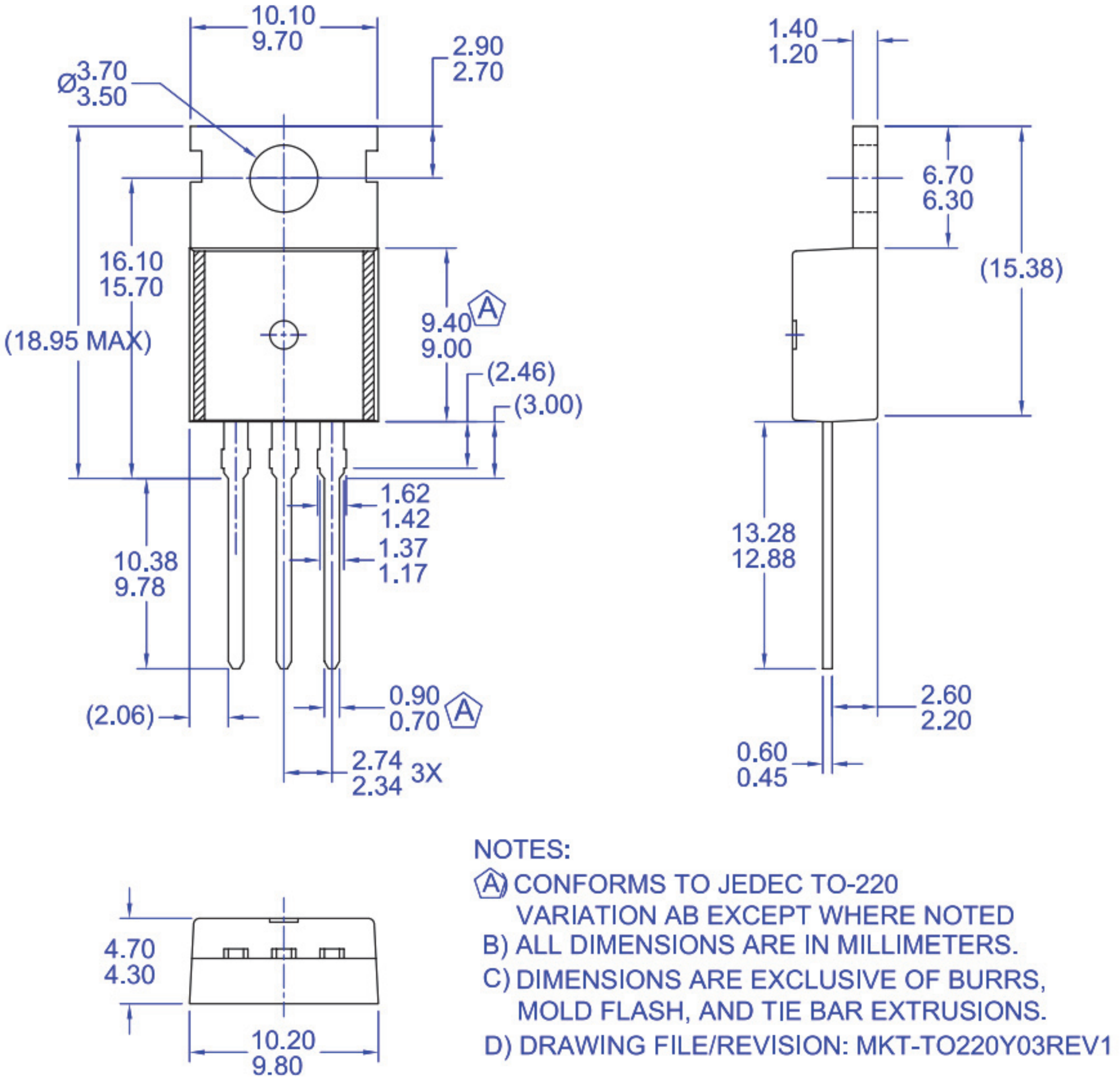


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES:

Ⓐ CONFORMS TO JEDEC TO-220 VARIATION AB EXCEPT WHERE NOTED

B) ALL DIMENSIONS ARE IN MILLIMETERS.

C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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